

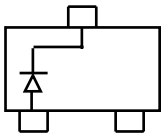
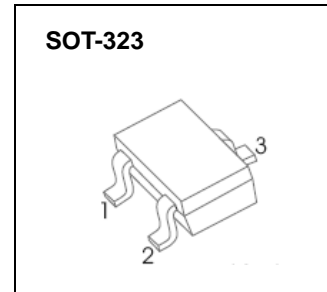


## Plastic-Encapsulate Diodes

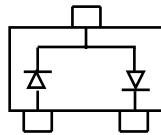
SCHOKKTY BARRIER DIODE

### FEATURES

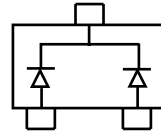
- Low turn-on voltage
- Fast switching
- Also available in lead free version



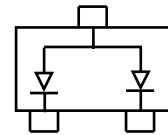
BAS70W Marking: K73



BAS70W-04 Marking: K74



BAS70W-05 Marking: K75



BAS70W-06 Marking: K76

### MARKING:

BAS70W	BAS70W-04	BAS70W-05	BAS70W-06

Solid dot = Green molding compound device, if none, the normal device.

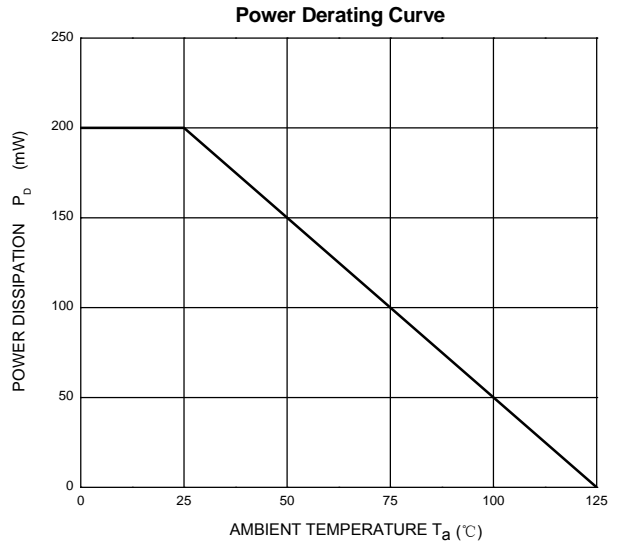
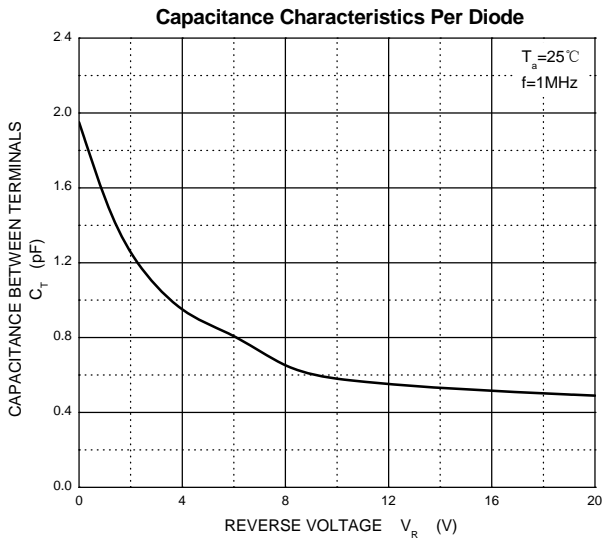
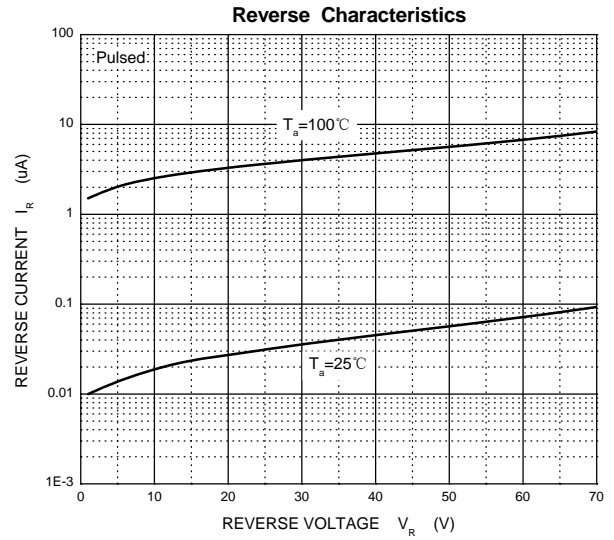
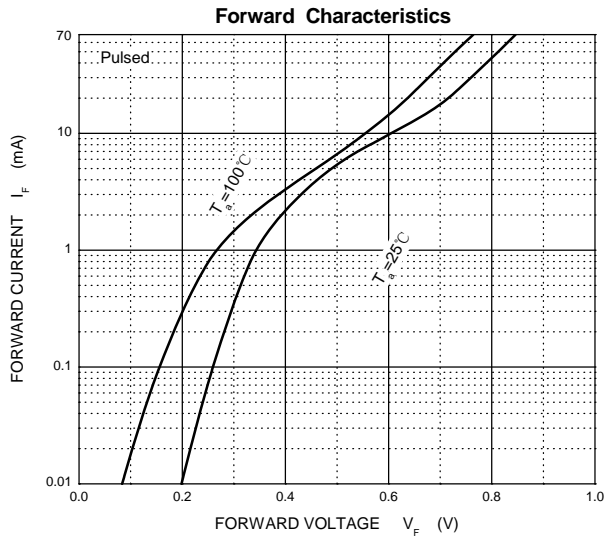
### MAXIMUM RATINGS @T<sub>a</sub>=25°C

Symbol	Parameter	Value	Unit
V <sub>R</sub>	DC Voltage	70	V
I <sub>F</sub>	Forward Continuous Current	70	mA
I <sub>FSM</sub>	Non-Repetitive Peak Forward Surge Current @ t = 8.3ms	100	mA
P <sub>D</sub>	Power Dissipation	200	mW
R <sub>θJA</sub>	Thermal Resistance from Junction to Ambient	500	°C/W
T <sub>J</sub>	Junction Temperature	125	°C
T <sub>stg</sub>	Storage Temperature	-55~+150	°C

### ELECTRICAL CHARACTERISTICS (T<sub>a</sub>=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Max	Unit
Reverse breakdown voltage	V <sub>(BR)</sub>	I <sub>R</sub> = 10μA	70		V
Reverse voltage leakage current	I <sub>R</sub>	V <sub>R</sub> =50V		100	nA
Forward voltage	V <sub>F</sub>	I <sub>F</sub> =1mA I <sub>F</sub> =15mA		410 1000	mV
Diode capacitance	C <sub>D</sub>	V <sub>R</sub> =0V, f=1MHz		2	pF
Reverse recovery time	t <sub>rr</sub>	I <sub>F</sub> =I <sub>R</sub> =10mA, I <sub>rr</sub> =0.1I <sub>R</sub> , R <sub>L</sub> =100Ω		5	ns

### Typical Characteristics





**CHINA BASE**  
INTERNATIONAL

**SOT-323**



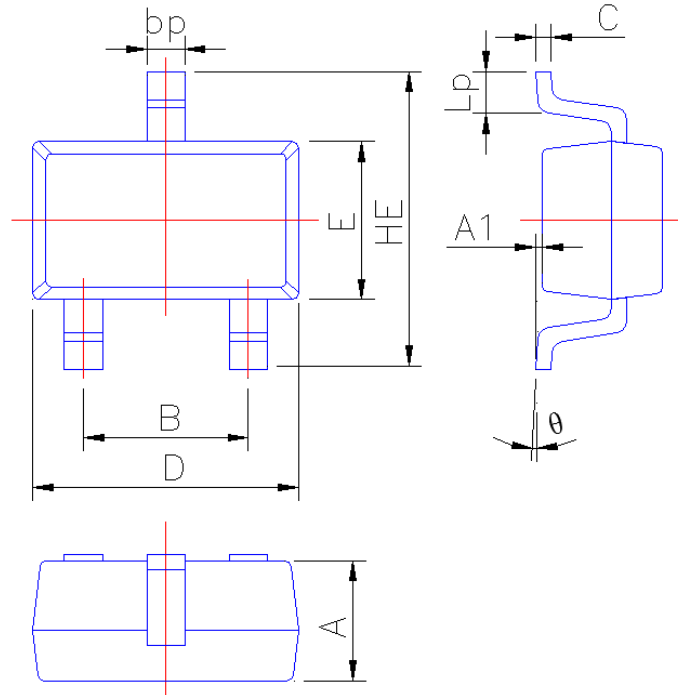
**BAS70W-04-05-06**

www.china-base.com.hk

**PACKAGE OUTLINE**

Plastic surface mounted package; 3 leads

SOT-323



Symbol	Dimension in Millimeters	
	Min	Max
A	0.90	1.00
A1	0.010	0.100
B	1.20	1.40
bp	0.25	0.45
C	0.09	0.15
D	2.00	2.20
E	1.15	1.35
HE	2.15	2.55
Lp	0.25	0.46
θ	0°	6°